

7 and 27

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	U	Inventor	Document	Issue	P	Title	Current	Current X	Retrieval	S	C	P	Image	Doc. P.
1		Lin, Qi et al.	US 6363016	20020	1	Method for enhancement of non-volatile me	365/185	365/185	18					US 6363016
2		Shor, Joseph	US 6507235	20030	1	Local substrate pumping in integrated circuit	327/534	327/564						US 6507235
3		Chen, Ih-Chin	US 5894145	18990	5	Multiple substrate bias random access memo	257/286	257/301						US 5894145
4		Etong, Jun et al	US RE37593	20020	1	Large scale integrated circuit with sense am	365/189	327/530						US RE37593
5		Kish, Tsu-Jae	US 2004003	20040	1	Negative differential resistance (NDR) based	365/202							US 2004003
6		Burr, James	US 2003020	20031	3	Device including a resistive path to introduce	257/536	257/E27.03						US 2003020
7		Burr, James	US 2003017	20030	3	Device including a resistive path to introduce	257/536	257/E27.03						US 2003017
8		Burr, James	US 2003017	20030	3	Device including a resistive path to introduce	257/369	257/371						US 2003017
9		Burr, James	US 2003017	20030	3	Device including a resistive path to introduce	257/369	257/371						US 2003017
10		Jang, Moon G	US 2003013	20030	8	Method of manufacturing nano transistors	438/694	257/E21.70						US 2003013
11		Doishi, Tsuka	US 2001001	20010	3	Semiconductor memory device	365/205							US 2001001
12		Burr, James	US 6800924	20041	3	Device including a resistive path to introduce	257/536	257/345						US 6800924
13		Jang, Moon G	US 6797629	20040	8	Method of manufacturing nano transistors	438/694	438/700						US 6797629
14		Burr, James	US 6781213	20040	3	Device including a resistive path to introduce	257/536	257/345						US 6781213

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